L Number	Hits	Search Text	DB	Time stamp
1	10	(semiconduct$3 same (defect$3 and (resist or photoresist or photopolymer$7) and develop$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/15 15:30
2	11	(((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) and (develop$4 or rins$3 or clean$3 or dry$3 or spin$4 or rotat$3 or turn$3) same (exhaust$3 or air or gas or sweep$ or flow$3 or pass$3) near5 (velocit$3 or speed$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/15 15:32
3	40	(((((resist or photoresist or photopolymer$7) same (develop$4 or rins$3 or clean$3 or remov$3 or residue or rubbish or debris) same (spin$4 or spun or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) not (((((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) and (develop$4 or rins$3 or clean$3 or dry$3 or spin$4 or rotat$3 or turn$3) same (exhaust$3 or air or gas or sweep$ or flow$3 or pass$3) near5 (velocit$3 or speed$3))) and (semiconduct$3 or wafer or silicon or "Si")) and (spin$4 or spun or rotat$3 or turn$3) same (exhaust$3 or air or sweep$3 or swept or inert or gas$4)) and (resist or photoresist or photopolym$7) same (prim$3 or pre adj treat$3 or pretreat$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/15 15:35
4	86	(((resist or photoresist or photopolymer$7) and (semiconduct$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim$3 or pretreat$4 or pre adj treat$4)) not ((semiconduct$3 same (defect$3 and (resist or photoresist or photopolymer$7) and develop$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim$3)) and (((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim$3) near5 vapor) same (seconds or "sec")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/10/15 15:37

| 5 | 148 | (430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer$7) same ((develop$4) and (rins$3 or wash$3 or clean$3 or remov$3 or residue or rubbish or debris)) same (spin$4 or spun or rotat$3 or turn$3)) not ((((((resist or photoresist or photopolymer$7) same (develop$4 or rins$3 or clean$3 or remov$3 or residue or rubbish or debris) same (spin$4 or spun or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) not ((((semiconduct$3 or silicon or "Si" or wafer) same ((defect$3 or residue) and (resist or photoresist or photopolymer$7) and develop$4)) and (resist or photoresist or photopolymer$7) same (develop$4 or rins$3) same (spin$4 or rotat$3 or turn$3) near5 (velocit$3 or speed$3)) and (develop$4 or rins$3 or clean$3 or dry$3 or spin$4 or rotat$3 or turn$3) same (exhaust$3 or air or gas or sweep$ or flow$3 or pass$3) near5 (velocit$3 or speed$3))) and (semiconduct$3 or wafer or silicon or "Si")) and (spin$4 or spun or rotat$3 or turn$3) same (exhaust$3 or air or sweep$3 or swept or inert or gas$4)) and (resist or photoresist or photopolym$7) same (prim$3 or pre adj treat$3 or pretreat$3)))) and (rins$3 or wash$3 or clean$3 or remov$3 or residue or rubbish or debris) same (revolution or "rpm") | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/10/15 15:55 |